

# DATA SHEET

Datasheet.Directory

## **PDTC114E series**

**NPN resistor-equipped transistor;**

**R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$**

Product specification  
Supersedes data of 2003 Apr 10

2004 Aug 05

## NPN resistor-equipped transistor; R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

## PDTC114E series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	10	–	k $\Omega$
R2	bias resistor	10	–	k $\Omega$

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC114EE	SOT416	SC-75	09	PDTA114EE
PDTC114EEF	SOT490	SC-89	09	PDTA114EEF
PDTC114EK	SOT346	SC-59	04	PDTA114EK
PDTC114EM	SOT883	SC-101	DS	PDTA114EM
PDTC114ES	SOT54 (TO-92)	SC-43	TC114E	PDTA114ES
PDTC114ET	SOT23	–	*16 <sup>(1)</sup>	PDTA114ET
PDTC114EU	SOT323	SC-70	*09 <sup>(1)</sup>	PDTA114EU

### Note

1. \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

NPN resistor-equipped transistor;  
 R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

**SIMPLIFIED OUTLINE, SYMBOL AND PINNING**

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC114ES		1 2 3	base collector emitter
PDTC114EE PDTC114EEF PDTC114EK PDTC114ET PDTC114EU		1 2 3	base emitter collector
PDTC114EM		1 2 3	base emitter collector

NPN resistor-equipped transistor;  
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## PDTC114E series

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	10	V
V <sub>I</sub>	input voltage				
		positive	–	+40	V
	negative		–	–10	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
SOT883	notes 2 and 3	–	250	mW	
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
SOT883	notes 2 and 3	500	K/W	

**Notes**

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

NPN resistor-equipped transistor;  
 $R1 = 10\text{ k}\Omega$ ,  $R2 = 10\text{ k}\Omega$

PDTC114E series

### CHARACTERISTICS

$T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{\text{CBO}}$	collector-base cut-off current	$V_{\text{CB}} = 50\text{ V}$ ; $I_{\text{E}} = 0$	–	–	100	nA
$I_{\text{CEO}}$	collector-emitter cut-off current	$V_{\text{CE}} = 30\text{ V}$ ; $I_{\text{B}} = 0$	–	–	1	$\mu\text{A}$
		$V_{\text{CE}} = 30\text{ V}$ ; $I_{\text{B}} = 0$ ; $T_{\text{j}} = 150\text{ }^{\circ}\text{C}$	–	–	50	$\mu\text{A}$
$I_{\text{EBO}}$	emitter-base cut-off current	$V_{\text{EB}} = 5\text{ V}$ ; $I_{\text{C}} = 0$	–	–	400	$\mu\text{A}$
$h_{\text{FE}}$	DC current gain	$V_{\text{CE}} = 5\text{ V}$ ; $I_{\text{C}} = 5\text{ mA}$	30	–	–	
$V_{\text{CEsat}}$	collector-emitter saturation voltage	$I_{\text{C}} = 10\text{ mA}$ ; $I_{\text{B}} = 0.5\text{ mA}$	–	–	150	mV
$V_{\text{i(off)}}$	input-off voltage	$I_{\text{C}} = 100\text{ }\mu\text{A}$ ; $V_{\text{CE}} = 5\text{ V}$	–	1.1	0.8	V
$V_{\text{i(on)}}$	input-on voltage	$I_{\text{C}} = 10\text{ mA}$ ; $V_{\text{CE}} = 0.3\text{ V}$	2.5	1.8	–	V
R1	input resistor		7	10	13	$\text{k}\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
$C_{\text{c}}$	collector capacitance	$I_{\text{E}} = i_{\text{e}} = 0$ ; $V_{\text{CB}} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	–	2.5	pF

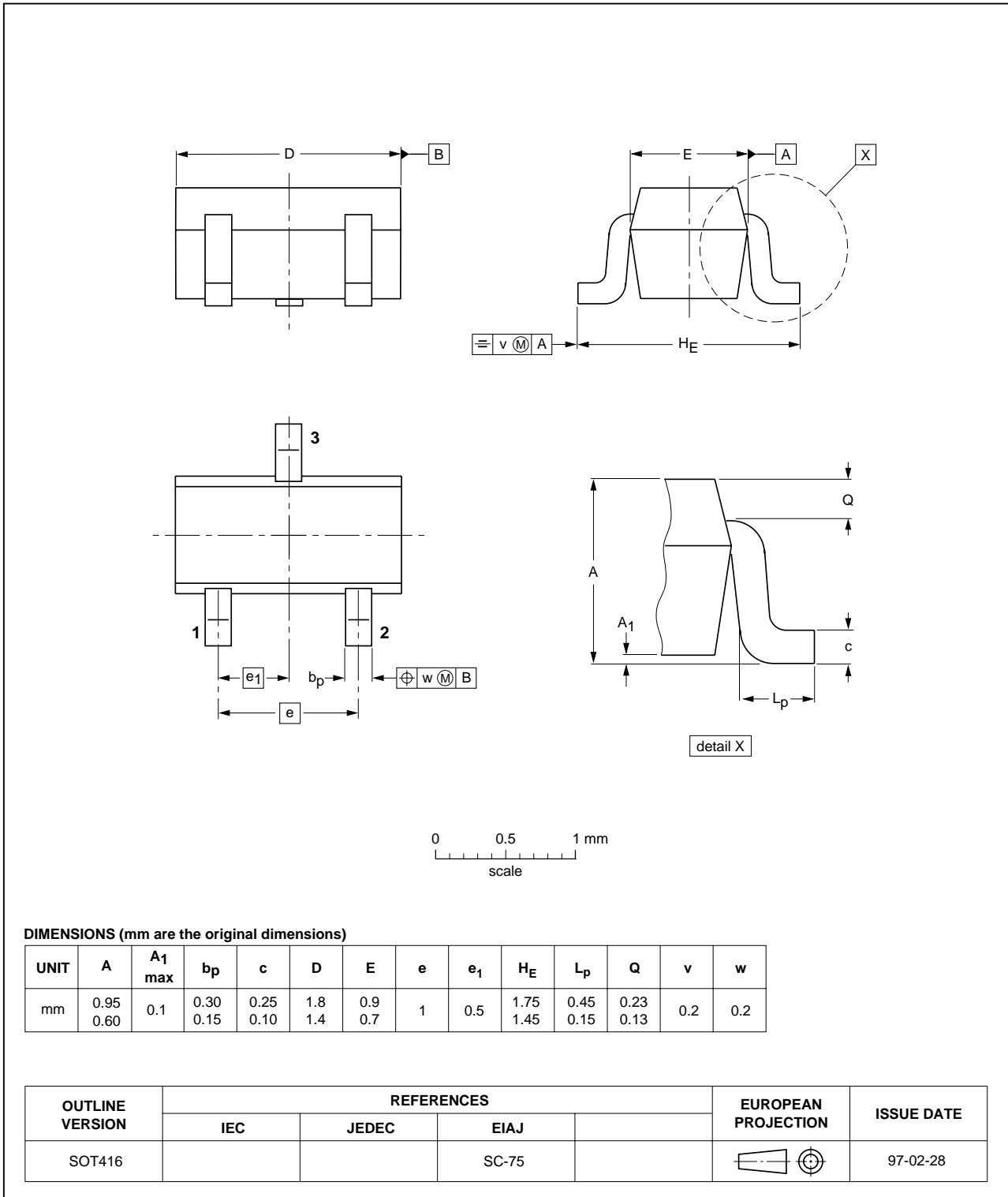
NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416

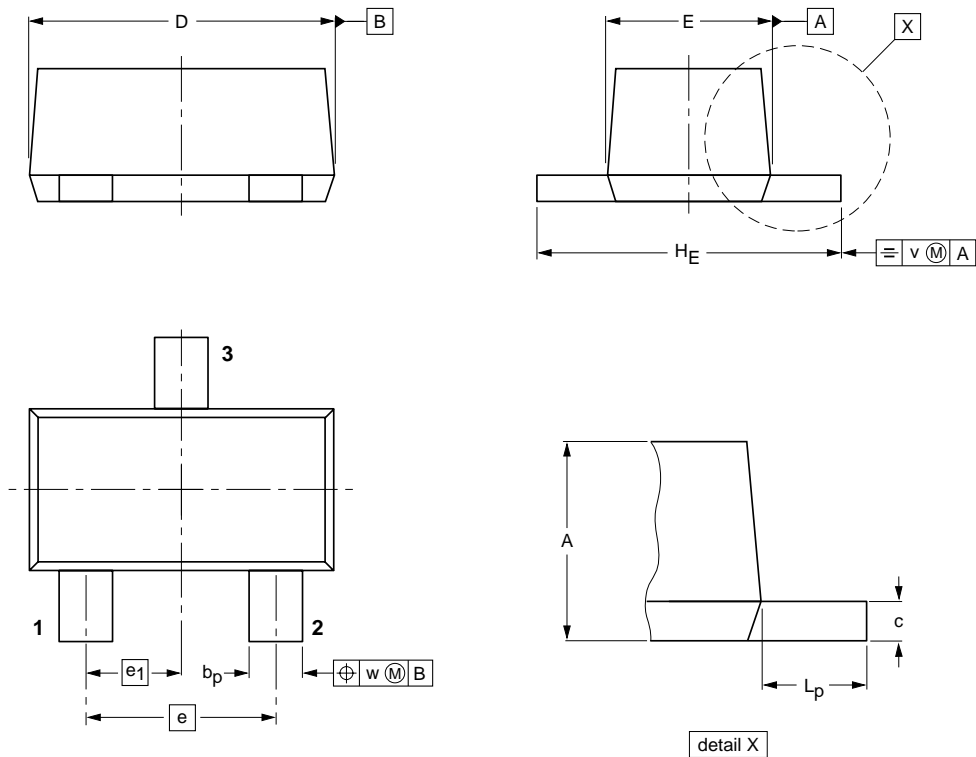


NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Plastic surface mounted package; 3 leads

SOT490



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

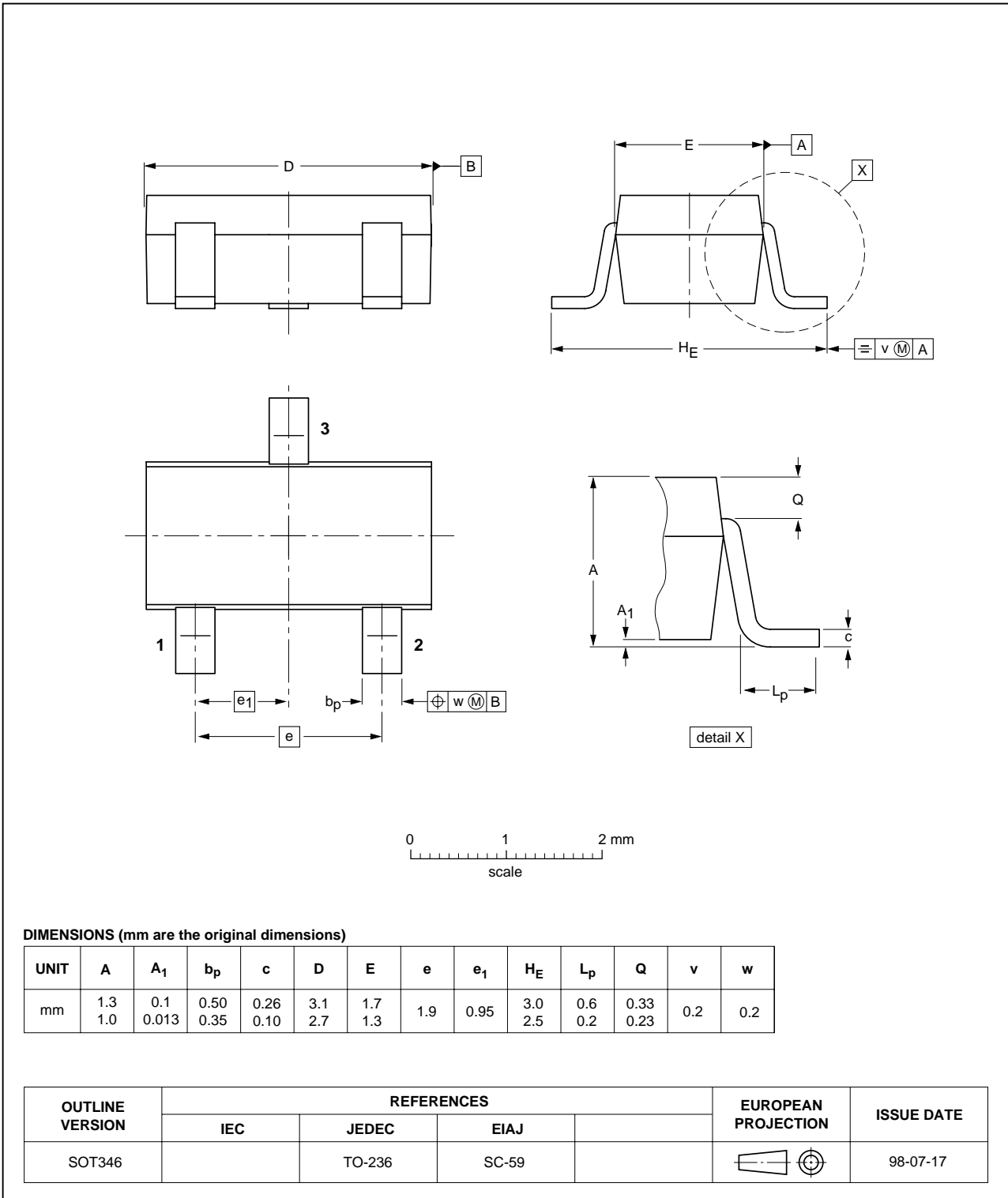
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT490			SC-89		98-10-23

NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Plastic surface mounted package; 3 leads

SOT346



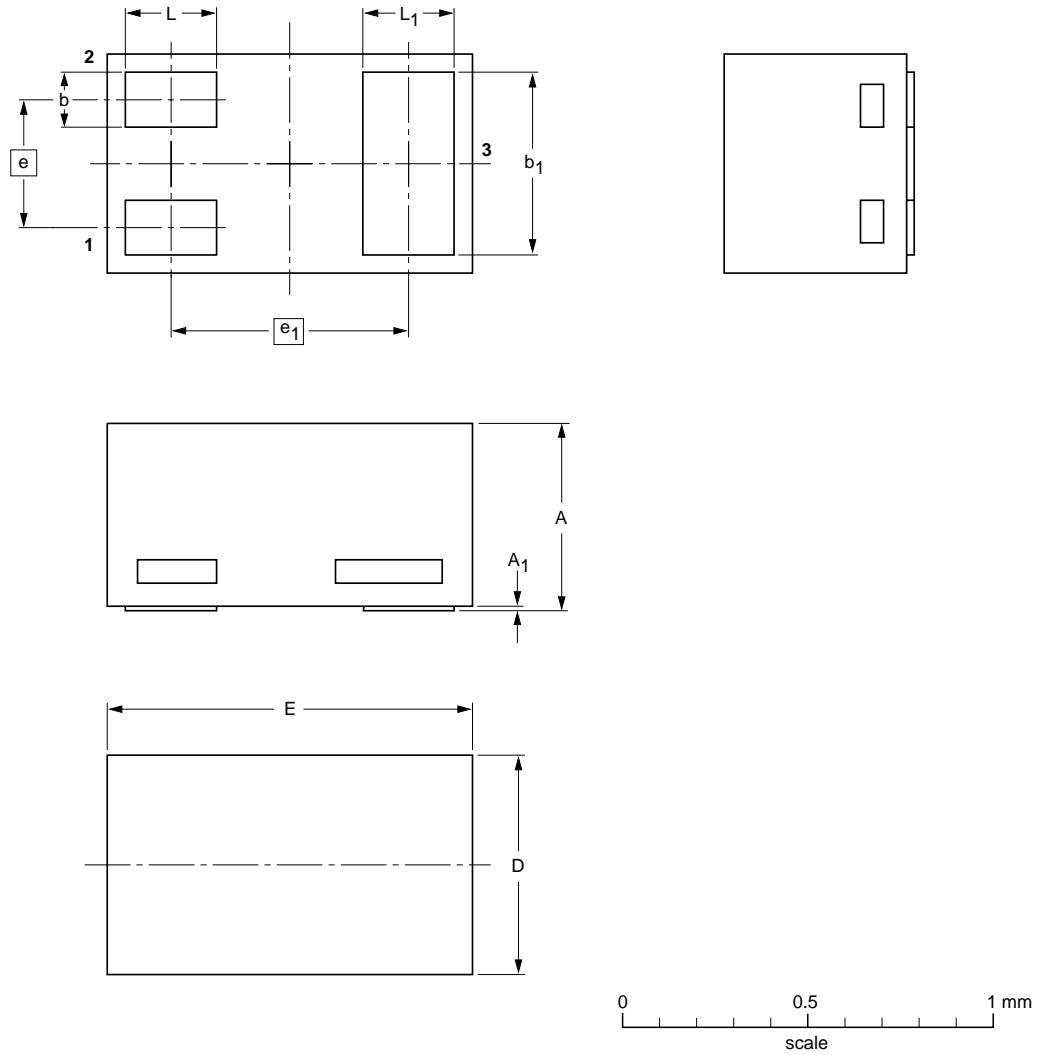


NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A <sup>(1)</sup>	A <sub>1</sub> max.	b	b <sub>1</sub>	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

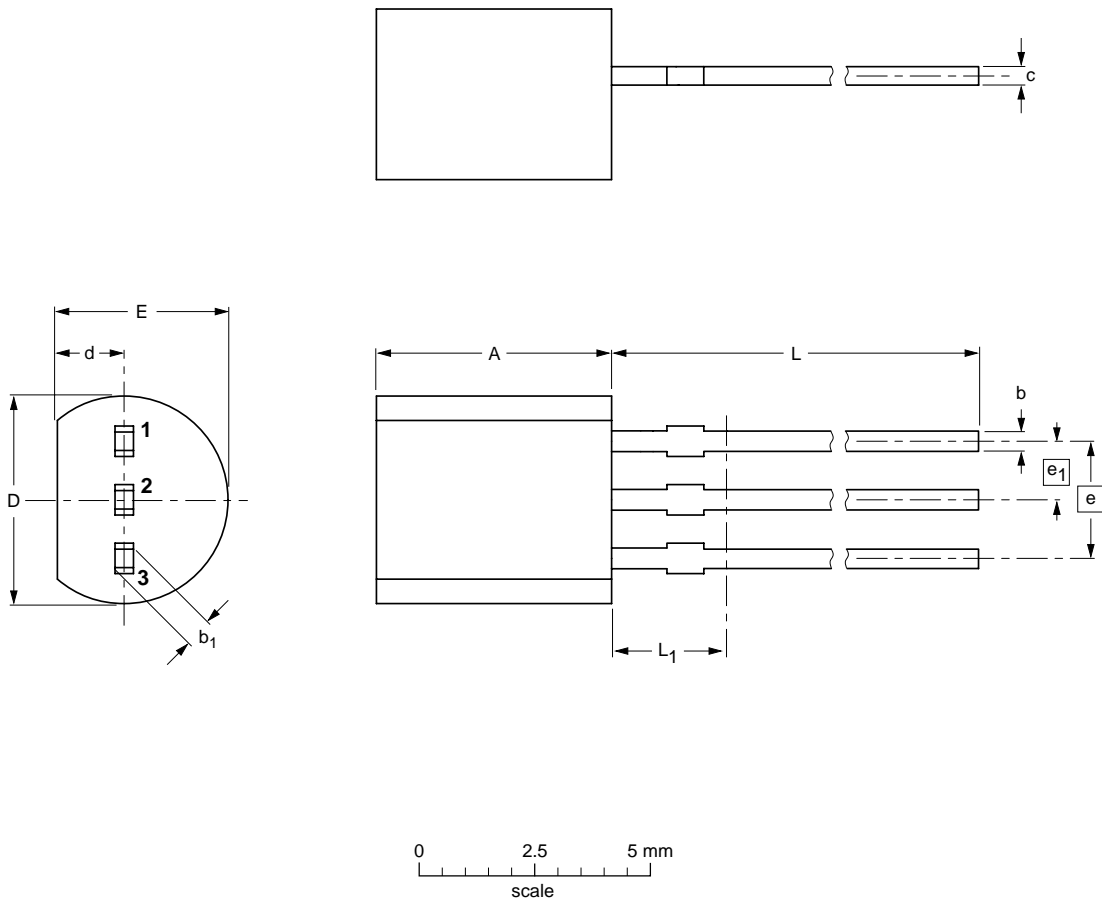
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

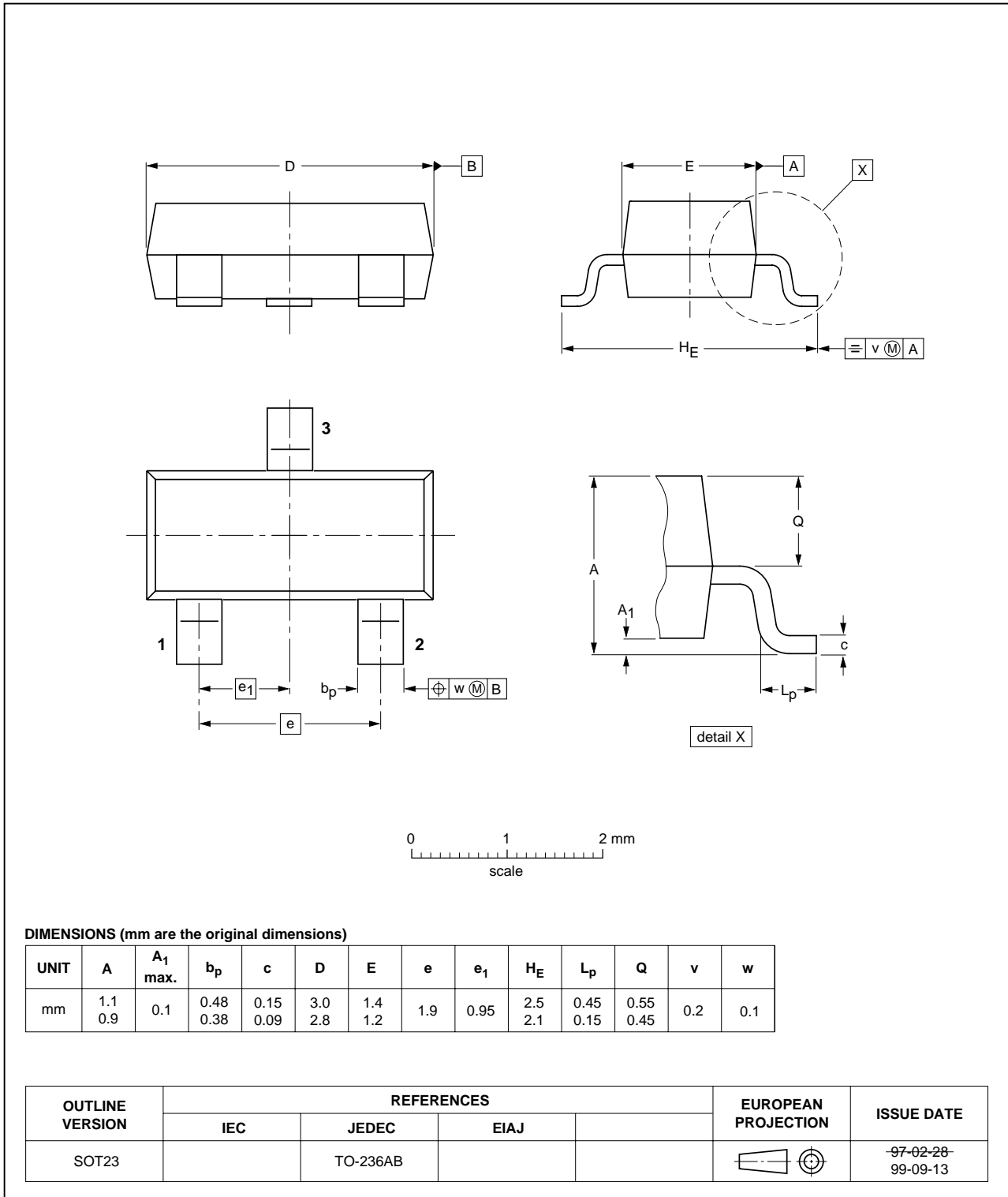
OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT54		TO-92	SC-43A		-97-02-28 04-06-28

NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Plastic surface mounted package; 3 leads

SOT23

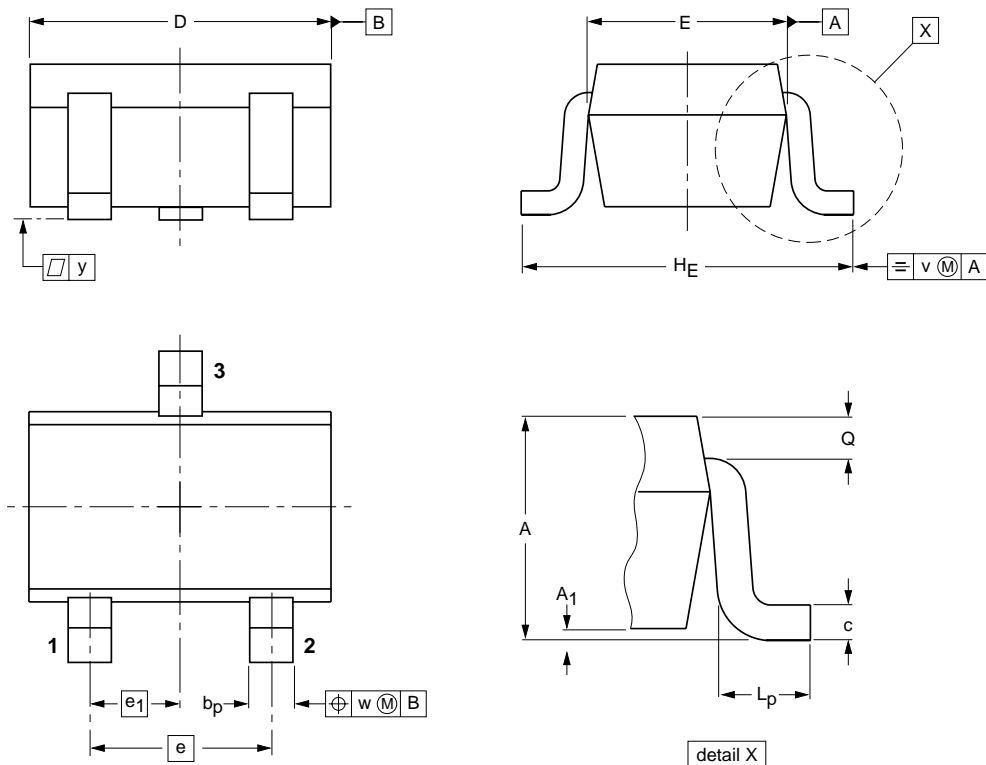


NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN resistor-equipped transistor;  
R1 = 10 kΩ, R2 = 10 kΩ

PDTC114E series

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## **Contact information**

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com).

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